

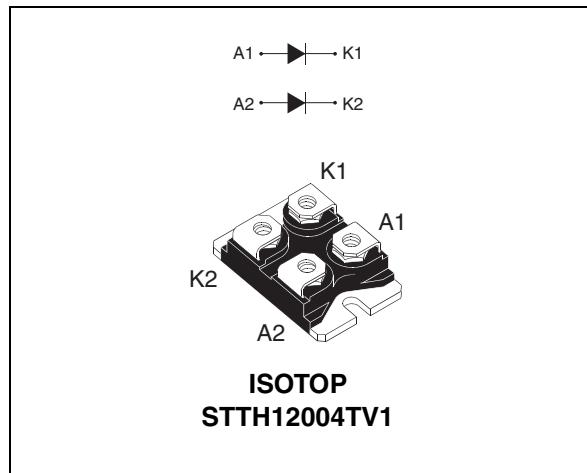
Ultrafast high voltage rectifier

Table 1: Main product characteristics

$I_{F(AV)}$	2 x 60 A
V_{RRM}	400 V
T_j (max)	150 °C
V_F (typ)	0.83 V
t_{rr} (max)	50 ns

Features and benefits

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching & conduction losses



Description

The STTH12004TV1 uses ST 400V technology and is specially suited for use in switching power supplies, welding equipment, and industrial applications, as an output rectification diode.

Table 2: Order codes

Part number	Marking
STTH12004TV1	STTH12004TV1

Table 3: Absolute ratings (limiting values, per diode)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	400	V
$I_{F(RMS)}$	RMS forward current	120	A
$I_{F(AV)}$	Average forward current	60	A
I_{FSM}	Surge non repetitive forward current	600	A
T_{stg}	Storage temperature range	-55 to + 150	°C
T_j	Maximum operating junction temperature	150	°C

STTH12004TV1

Table 4: Thermal resistance

Symbol	Parameter	Value (max.)	Unit
$R_{th(j-c)}$	Junction to case	Per diode	0.5
		Total	0.3
$R_{th(c)}$	Coupling	0.1	°C/W

When diodes 1 and 2 are used simultaneously:

$$\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)} (\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$$

Table 5: Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
I_R *	Reverse leakage current	$T_j = 25$ °C	$V_R = V_{RRM}$			50	µA
		$T_j = 125$ °C			50	500	
V_F **	Forward voltage drop	$T_j = 25$ °C	$I_F = 60$ A			1.2	V
		$T_j = 150$ °C			0.83	1.0	

Pulse test: * $t_p = 5$ ms, $\delta < 2\%$

** $t_p = 380$ µs, $\delta < 2\%$

To evaluate the conduction losses use the following equation: $P = 0.8 \times I_F(AV) + 0.0033 I_F^2$ (RMS)

Table 6: Dynamic characteristics (per diode)

Symbol	Parameter	Test conditions			Min	Typ	Max	Unit
t_{rr}	Reverse recovery time	$T_j = 25$ °C	$I_F = 1$ A	$dI_F/dt = 50$ A/µs	$V_R = 30$ V		66	90
			$I_F = 1$ A	$dI_F/dt = 200$ A/µs	$V_R = 30$ V		36	50
I_{RM}	Reverse recovery current	$T_j = 125$ °C	$I_F = 60$ A $V_R = 200$ V $dI_F/dt = 100$ A/µs				15	A
S_{factor}	Softness factor	$T_j = 125$ °C	$I_F = 60$ A $V_R = 200$ V $dI_F/dt = 100$ A/µs			0.4		
t_{fr}	Forward recovery time	$T_j = 25$ °C	$I_F = 60$ A $dI_F/dt = 200$ A/µs $V_{FR} = 1.1 \times V_{Fmax}$				600	ns
V_{FP}	Forward recovery voltage	$T_j = 25$ °C	$I_F = 60$ A $dI_F/dt = 200$ A/µs $V_{FR} = 1.1 \times V_{Fmax}$			2.6		V

Figure 1: Conduction losses versus average forward current (per diode)

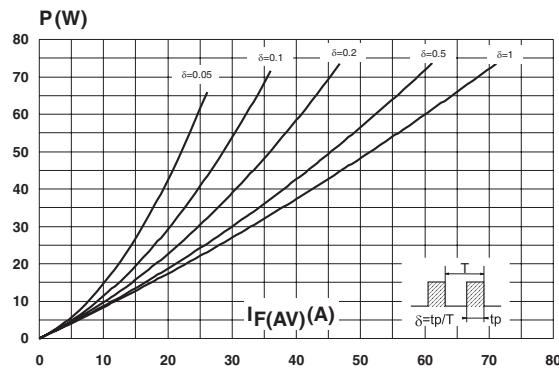


Figure 2: Forward voltage drop versus forward current (per diode)

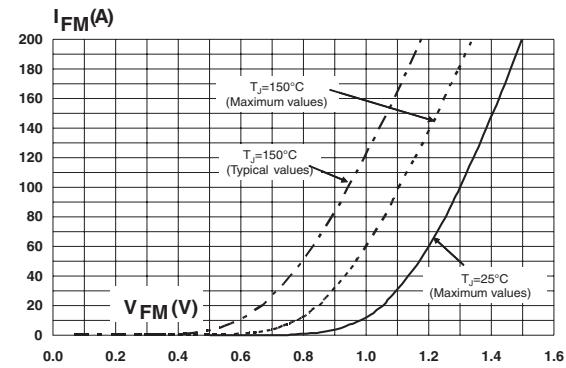


Figure 3: Relative variation of thermal impedance junction to case versus pulse duration

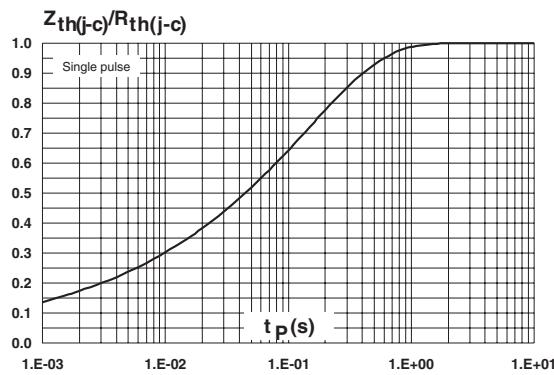


Figure 4: Peak reverse recovery current versus dI_F/dt (typical values, per diode)

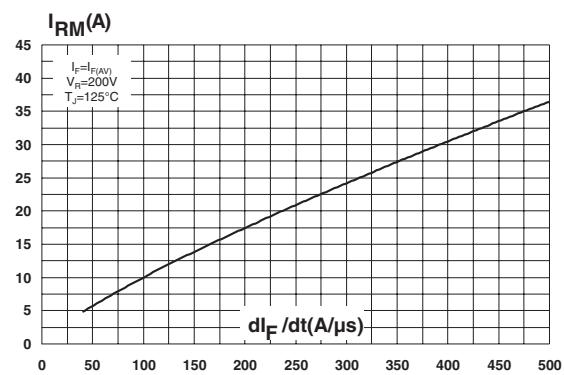


Figure 5: Reverse recovery time versus dI_F/dt (typical values, per diode)

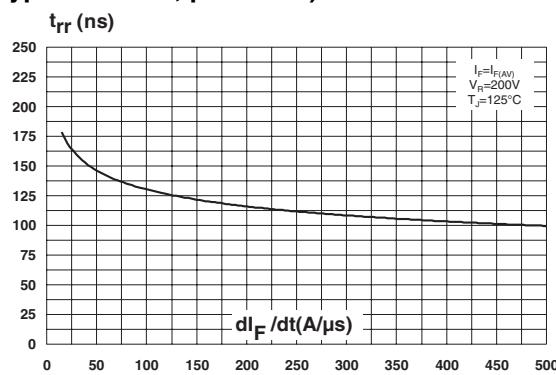
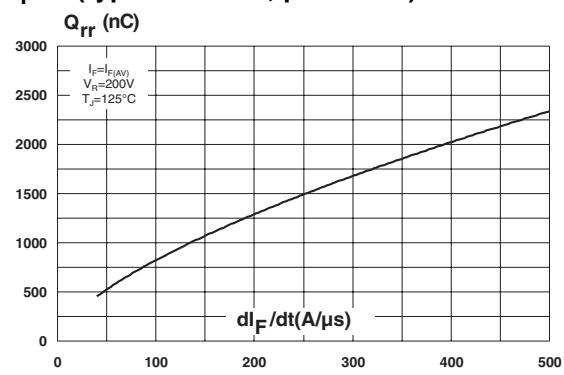


Figure 6: Reverse recovery charges versus dI_F/dt (typical values, per diode)



STTH12004TV1

Figure 7: Reverse recovery softness factor versus dI_F/dt (typical values, per diode)

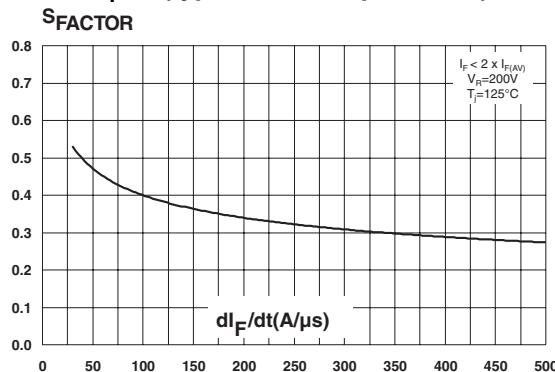


Figure 8: Relative variations of dynamic parameters versus junction temperature

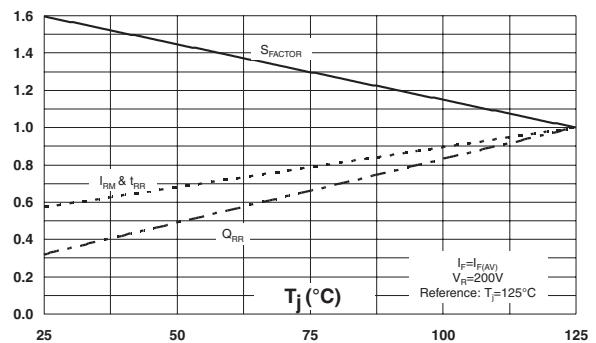


Figure 9: Transient peak forward voltage versus dI_F/dt (typical values, per diode)

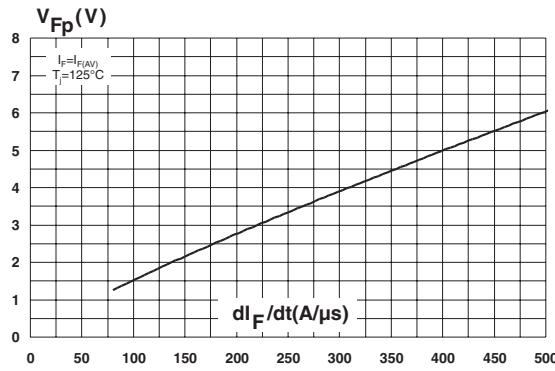


Figure 10: Forward recovery time versus dI_F/dt (typical values, per diode)

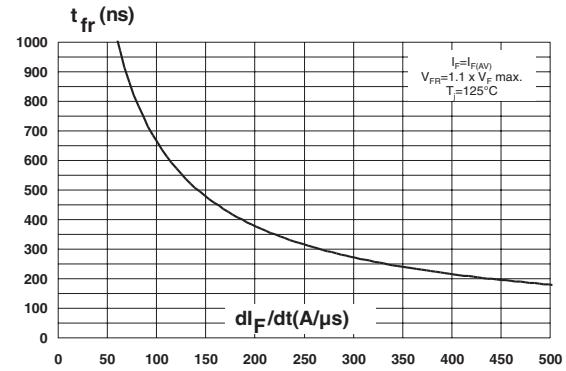


Figure 11: Junction capacitance versus reverse voltage applied (typical values, per diode)

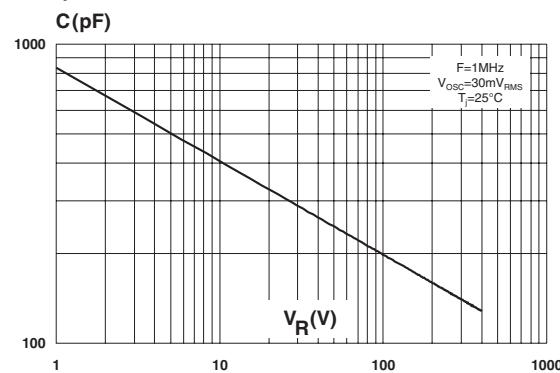


Figure 12: ISOTOP Package mechanical data

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
B	7.8	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80 typ.		0.976 typ.	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5.00	0.181	0.197
P	4.00	4.30	0.157	0.69
P1	4.00	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Table 7: Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH12004TV1	STTH12004TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

Table 8: Revision history

Date	Revision	Description of Changes
18-Oct-2005	1	First issue

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics.
All other names are the property of their respective owners

© 2005 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -
Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America
www.st.com